

Amendments to the Claims:

This listing of claims replaces all prior versions and listings of claims in the application:

Listing of Claims:

1. (Currently amended) A semiconductor device comprising:
a pixel matrix circuit including at least ~~a plurality of~~ source lines; ~~a plurality of~~ and gate lines;
a driver circuit including at least a source line driver circuit for driving the source lines and a gate line driver circuit for driving the gate lines; and
a logic circuit for processing a signal required for driving the driver circuit and a signal including image information transmitted to the pixel matrix circuit,
wherein the pixel matrix circuit, the driver circuit and the logic circuit are disposed over ~~a~~ the same substrate,
wherein the pixel matrix circuit, the driver circuit, and the logic circuit are constituted by a plurality of thin film transistors, each having an active layer comprising crystalline silicon, ~~and~~
wherein the active layer of each of said ~~the~~ plurality of thin film transistors ~~comprise~~ comprises a plurality of rod-shaped crystals extending in one direction, and
wherein the logic circuit includes at least one or more selected from the group consisting of a phase comparator, a LPF (low pass filter), a VCO (voltage controlled oscillator), a frequency divider, a horizontal scanning oscillator, a vertical scanning oscillator, a D/A converter, an I/O port, a differential amplifier, an operational amplifier, a comparator and a memory.

2. (Currently amended) A The semiconductor device according to claim 1, wherein crystal lattices said of the plurality of rod-shaped crystals are continuous within each of the active layer layers so that there is no barrier for carriers within each of the active layer layers.

3. (Currently amended) A The semiconductor device according to claim 1, wherein said the semiconductor device is a liquid crystal display.

4. (Currently amended) A The semiconductor device according to claim 1, wherein said each of the plurality of rod-shaped crystals have has a flattened shape.

5. (Currently amended) A The semiconductor device according to claim 1, wherein said the active layer has an anisotropy between a channel length direction and a channel width direction thereof.

6. (Currently amended) A The semiconductor device according to claim 1, wherein said the active layer includes an intrinsic or substantially intrinsic channel forming region.

7. (Currently amended) A The semiconductor device according to claim 1, wherein said the active layer contains an element selected from the group consisting of Ni, Fe, Co, Sn, Pd, Pb, Pt, Cu and Au at a concentration 1×10^{17} atoms/cm³ or lower, said the element being capable of promoting crystallization of silicon.

8. (Currently amended) A The semiconductor device according to claim 1, wherein said the active layer contains an element selected from the group consisting of Cl, F, and Br at a concentration from 1×10^{15} to 1×10^{20} atoms/cm³.

9. (Currently amended) A The semiconductor device according to claim 8, wherein said the element is concentrated at a portion close to a gate insulating film.

10. (Currently amended) A The semiconductor device according to claim 1, wherein said the pixel matrix circuit has a plurality of pixels, and each of said the plurality of pixels is provided with at least two of said the plurality of thin film transistors connected in series.

11. (Currently amended) A The semiconductor device according to claim 1, wherein said the pixel matrix circuit has a plurality of pixels, each of which is provided with a storage capacitor formed between a connect wiring and a black mask.

12. (Currently amended) A The semiconductor device according to claim 11, further comprising an organic film having an opening wherein said the black mask is formed on said the organic film and said the storage capacitor is formed within said the opening.

13. (Currently amended) A The semiconductor device according to claim 11, wherein said the connect wiring comprises a the same material as a source electrode of each of said the plurality of thin film transistors, and said the connect wiring is formed from a the same layer as said the source electrode.

14. (Currently amended) A The semiconductor device according to claim 1, wherein one of said the plurality of thin film transistors constituting said the pixel matrix circuit has a different dimension from one of said the plurality of thin film transistors constituting at least one of said the driver circuit and said the logic circuit.

15. (Canceled)

16. (Currently amended) A semiconductor device comprising:
a pixel circuit;
a driver circuit for driving said the pixel circuit; and
a logic circuit for processing a signal required for driving the driver circuit;
wherein said the pixel circuit, said the driver circuit and said the logic circuit are formed over a the same substrate and constituted with a plurality of N-channel type thin film transistors and a plurality of P-channel type thin film transistors;

wherein subthreshold coefficients of said the plurality of N-channel thin film transistors and said the plurality of P-channel thin film transistors are ~~both~~ within a range of 60 to 100 mV/decade, and

wherein the logic circuit includes at least one selected from the group consisting of a phase comparator, a low pass filter, a voltage controlled oscillator, a frequency divider, an oscillator for a source line driver and an oscillator for a gate line driver.

17. (Currently amended) A The semiconductor device according to claim 16, wherein said the pixel circuit has a plurality of pixels arrayed in rows and columns.

18. (Currently amended) A semiconductor device comprising:
a pixel matrix circuit including at least ~~a plurality of~~ source lines; and a plurality of gate lines;

a driver circuit including at least a source line driver circuit for driving the source lines and a gate line driver circuit for driving the gate lines; and

a logic circuit for processing a signal required for driving the driver circuit and a signal including image information transmitted to the pixel matrix circuit,

wherein the pixel matrix circuit, the driver circuit and the logic circuit are disposed over a the same substrate,

wherein the pixel matrix circuit, the driver circuit, and the logic circuit are constituted by a plurality of thin film transistors, each having an active layer comprising crystalline silicon,

wherein dimensions of said the plurality of thin film transistors are made different depending upon required electrical characteristics ~~by said circuits~~, and

wherein the logic circuit includes at least one selected from the group consisting of a phase comparator, a low pass filter, a voltage controlled oscillator, a frequency divider, an oscillator for a the source line driver circuit and an oscillator for a the gate line driver circuit.

19. (Currently amended) A The semiconductor device according to claim 18, wherein said the dimensions include at least one of a channel length and a thickness of a gate insulating film.

20. (Currently amended) A semiconductor device comprising:
a pixel matrix circuit including at least a plurality of source lines; a plurality of and gate lines;
a driver circuit including at least a source line driver circuit for driving the source lines and a gate line driver circuit for driving the gate lines; and
a logic circuit for processing a signal required for driving the driver circuit and a signal including image information transmitted to the pixel matrix circuit,
wherein the pixel matrix circuit, the driver circuit and the logic circuit are disposed over a the same substrate,
wherein the pixel matrix circuit, the driver circuit, and the logic circuit are constituted by a plurality of thin film transistors, each having an active layer comprising crystalline silicon,
wherein a thickness of a first gate insulating film of one of the plurality of thin film transistors which are is required to drive a circuit at 0.1 GHz or higher is 500 . or thinner, and a thickness of a second gate insulating film of one of the plurality of thin film transistors which are is driven by an operation voltage of 10V or greater is 1000 . or thicker, and
wherein the logic circuit includes at least one selected from the group consisting of a phase comparator, a low pass filter, a voltage controlled oscillator, a frequency divider, an oscillator for a the source line driver circuit and an oscillator for a the gate line driver circuit.

21. (Currently amended) An active matrix display comprising:
a pixel matrix circuit including at least a plurality of source lines; a plurality of and gate lines; and a plurality of TFTs;
a driver circuit including at least a source line driver circuit for driving the source lines and a gate line driver circuit for driving the gate lines; and

a logic circuit for processing a signal required for driving the driver circuit and a signal including image information transmitted to the pixel matrix circuit,

wherein the pixel matrix circuit, the driver circuit and the logic circuit are disposed ~~on~~ over the same substrate,

wherein the pixel matrix circuit, the driver circuit, and the logic circuit are constituted by a plurality of TFTs thin film transistors each ~~made of~~ comprising a crystalline silicon thin film,

wherein a plurality of circuits constituting the pixel matrix circuit, the driver circuit and the logic circuit include at least two kinds of circuits which are different from each other in at least one of a driving frequency and an operating voltage, and

wherein the logic circuit includes at least one selected from the group consisting of a phase comparator, a low pass filter, a voltage controlled oscillator, a frequency divider, an oscillator for a the source line driver circuit and an oscillator for a the gate line driver circuit.

22. (Currently amended) The semiconductor device according to claim 1, wherein ~~said~~ the semiconductor device is an EL display.

23. (Currently amended) The semiconductor device according to claim 16, wherein ~~said~~ the semiconductor device is an EL display.

24. (Currently amended) The semiconductor device according to claim 18, wherein ~~said~~ the semiconductor device is an EL display.

25. (Currently amended) The semiconductor device according to claim 20, wherein ~~said~~ the semiconductor device is an EL display.

26. (Currently amended) The semiconductor device according to claim 21, wherein ~~said~~ the semiconductor device is an EL display.